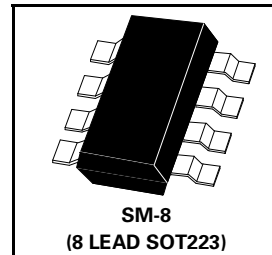
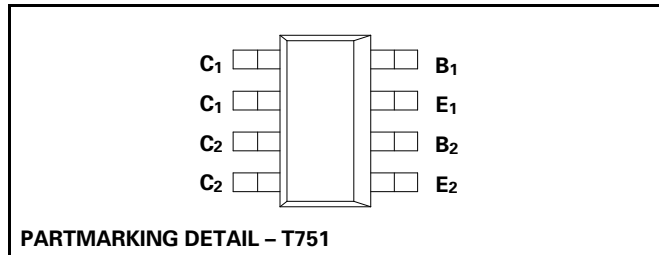


SM-8 DUAL PNP MEDIUM POWER TRANSISTORS

ISSUE 1 - AUGUST 1997

ZDT751



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-6	A
Continuous Collector Current	I_C	-2	A
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE	UNIT
Total Power Dissipation at $T_{amb} = 25^\circ\text{C}^*$ Any single die "on" Both die "on" equally	P_{tot}	2.25 2.75	W W
Derate above 25°C^* Any single die "on" Both die "on" equally		18 22	mW/°C mW/°C
Thermal Resistance - Junction to Ambient* Any single die "on" Both die "on" equally		55.6 45.5	°C/W °C/W

* The power which can be dissipated assuming the device is mounted in a typical manner on a PCB with copper equal to 2 inches square.



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ZDT751

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-80			V	$I_C = -100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60			V	$I_C = -10\text{mA}, I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CBO}			-0.1 -10	μA μA	$V_{CB} = -60\text{V}$ $V_{CB} = -60\text{V}, T_{amb} = 100^{\circ}\text{C}$
Emitter Cutoff Current	I_{EBO}			-0.1	μA	$V_{EB} = -4\text{V}, I_E = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.15 -0.28	-0.3 -0.5	V V	$I_C = 1\text{A}, I_B = -100\text{mA}^*$ $I_C = 2\text{A}, I_B = -200\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	-1.25	V	$I_C = 1\text{A}, I_B = -100\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.8	-1	V	$I_C = -1\text{A}, V_{CE} = -2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	70 100 80 40	200 200 170 80	300		$I_C = -50\text{mA}, V_{CE} = -2\text{V}^*$ $I_C = -500\text{mA}, V_{CE} = -2\text{V}^*$ $I_C = -1\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -2\text{A}, V_{CE} = -2\text{V}^*$
Transition Frequency	f_T	100	140		MHz	$I_C = -100\text{mA}, V_{CE} = -5\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}			30	pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$
Switching Times	t_{on}		40		ns	$I_C = -500\text{mA}, V_{CC} = -10\text{V}$ $I_{B1} = I_{B2} = -50\text{mA}$
	t_{off}		450		ns	

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

ZDT751

TYPICAL CHARACTERISTICS

